

# **TSM2301**

# 20V P-Channel MOSFET



**SOT-23** 

# 3 1 2

#### Pin Definition:

- 1. Gate
- 2. Source
- 3. Drain

### PRODUCT SUMMARY

V <sub>DS</sub> (V)	$R_{DS(on)}(m\Omega)$	I <sub>D</sub> (A)
-20	130 @ V <sub>GS</sub> = -4.5V	-2.8
	190 @ V <sub>GS</sub> = -2.5V	-2.0

### **Features**

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

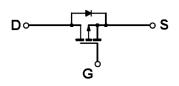
## **Application**

- Load Switch
- PA Switch

# **Ordering Information**

Part No.	Package	Packing
TSM2301CX RF	SOT-23	3Kpcs / 7" Reel

# **Block Diagram**



P-Channel MOSFET

# **Absolute Maximum Rating** (Ta = 25°C unless otherwise noted)

Parameter	ameter			Unit
Drain-Source Voltage		V <sub>DS</sub>	-20	V
Gate-Source Voltage		$V_{GS}$	±8	V
Continuous Drain Current, V <sub>GS</sub> @4.5V		I <sub>D</sub> -2.8		Α
Pulsed Drain Current, V <sub>GS</sub> @4.5V		I <sub>DM</sub>	-8	Α
Continuous Source Current (Diode Co	nduction) <sup>a,b</sup>	I <sub>S</sub>	-0.72	Α
Maximum Power Dissipation	Ta = 25°C	- P <sub>D</sub>	0.9	10/
	Ta = 75°C		0.57	W
Operating Junction Temperature		$T_J$	+150	°C
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	- 55 to +150	°C

## **Thermal Performance**

Parameter	Symbol	Limit	Unit
Lead Temperature (1/8" from case)	T <sub>L</sub>	5	S
Junction to Ambient Thermal Resistance (PCB mounted)	R⊖ <sub>JA</sub>	120	°C/W

#### Notes:

- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on FR4 Board,  $t \le 5$  sec.
- c. Surface Mounted on FR4 Board,



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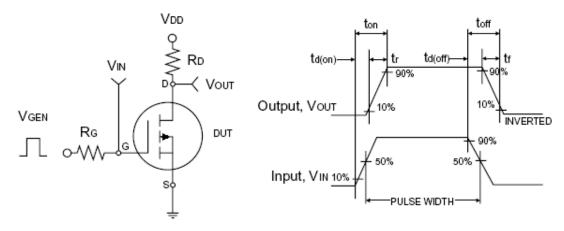


## **Electrical Specifications** (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_{D} = -250uA$	BV <sub>DSS</sub>	-20			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	$V_{GS(TH)}$	-0.45		-0.95	V
Gate Body Leakage	$V_{GS} = \pm 8V, V_{DS} = 0V$	I <sub>GSS</sub>			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = -9.6V, V_{GS} = 0V$	I <sub>DSS</sub>			-1.0	μA
On-State Drain Current <sup>a</sup>	$V_{DS} = -10V, V_{GS} = -5V$	I <sub>D(ON)</sub>	-6			Α
Drain-Source On-State Resistance	$V_{GS} = -4.5V$ , $I_D = -2.8A$	Ь		85	130	mΩ
Drain-Source On-State Resistance	$V_{GS} = -2.5V, I_D = -2.0A$	R <sub>DS(ON)</sub>	-	122	190	
Forward Transconductance <sup>a</sup>	$V_{DS} = -5V, I_{D} = -4A$	g <sub>fs</sub>	-	6.5		S
Diode Forward Voltage	$I_S = -0.75A$ , $V_{GS} = 0V$	$V_{SD}$	-	- 0.8	-1.2	V
Dynamic <sup>b</sup>						
Total Gate Charge	V - CV I - C O A	$Q_g$		5.4	10	nC
Gate-Source Charge	$V_{GS} = -2.5V, I_D = -2.0A$ $V_{DS} = -5V, I_D = -4A$	$Q_gs$		0.8		
Gate-Drain Charge	V <sub>GS</sub> = -4.5 V	$Q_{gd}$		1.1		
Input Capacitance	27. 27. 27.	C <sub>iss</sub>		447		
Output Capacitance		C <sub>oss</sub>		127		pF
Reverse Transfer Capacitance	1 - 1.0WINZ	C <sub>rss</sub>	1	80		
Switching <sup>c</sup>						
Turn-On Delay Time	N 0V D 00	$t_{d(on)}$		5	25	
Turn-On Rise Time	$V_{DD} = -6V, R_L = 6\Omega,$ $I_D = -1A, V_{GEN} = -4.5V,$	t <sub>r</sub>		19	60	nS
Turn-Off Delay Time	$R_{G} = 6\Omega$	$t_{d(off)}$	1	95	110	113
Turn-Off Fall Time	116 022	t <sub>f</sub>		65	80	

#### Notes:

- a. pulse test: PW =300 $\mu$ S, duty cycle =2%
- b. For DESIGN AID ONLY, not subject to production testing.
- b. Switching time is essentially independent of operating temperature.



**Switching Test Circuit** 

Switchin Waveforms



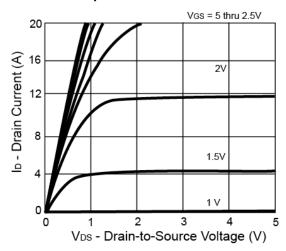




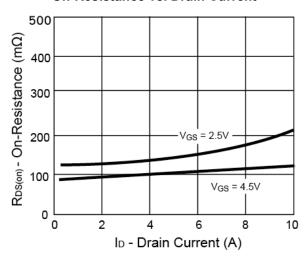


## Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

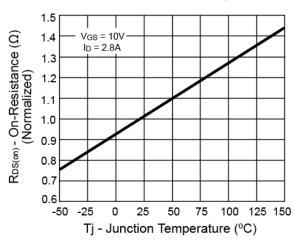




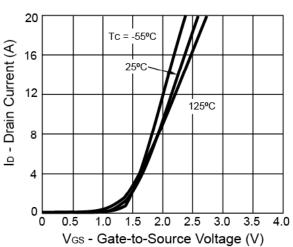
#### **On-Resistance vs. Drain Current**



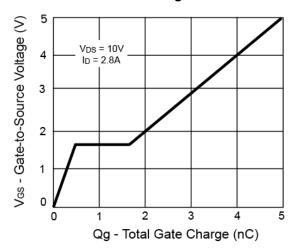
#### On-Resistance vs. Junction Temperature



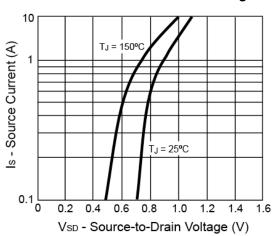
#### **Transfer Characteristics**



### **Gate Charge**



#### Source-Drain Diode Forward Voltage





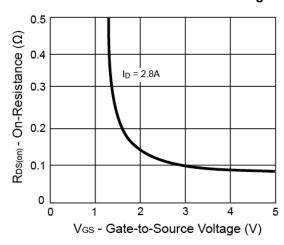




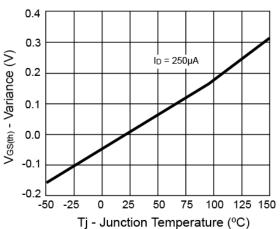


## **Electrical Characteristics Curve** (Ta = 25°C, unless otherwise noted)

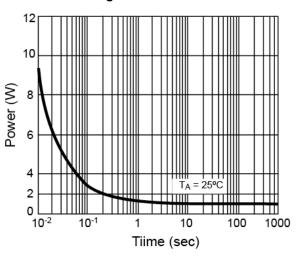
### On-Resistance vs. Gate-Source Voltage



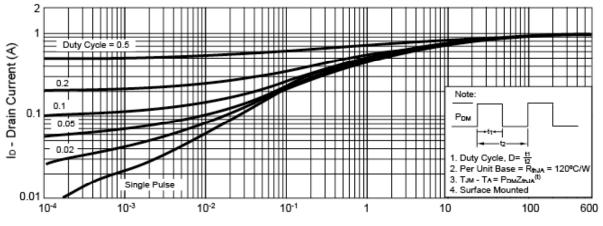
# Threshold Voltage



### Single Pulse Power



### Normalized Thermal Transient Impedance, Junction-to-Ambient



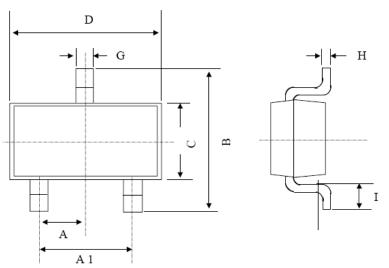
Square Wave Pulse Duration (sec)



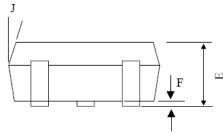




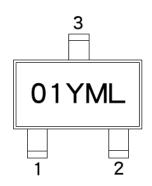
# **SOT-23 Mechanical Drawing**



227 22 211 (212)					
SOT-23 DIMENSION					
DIM	MILLIMETERS		INCHES		
DIIVI	MIN	MAX	MIN	MAX.	
Α	0.95	BSC	0.037	BSC	
A1	1.9 I	BSC	0.074	BSC	
В	2.60	3.00	0.102	0.118	
С	1.40	1.70	0.055	0.067	
D	2.80	3.10	0.110	0.122	
Е	1.00	1.30	0.039	0.051	
F	0.00	0.10	0.000	0.004	
G	0.35	0.50	0.014	0.020	
Н	0.10	0.20	0.004	0.008	
I	0.30	0.60	0.012	0.024	
J	5°	10°	5°	10°	



# **Marking Diagram**



01 = Device Code

Y = Year Code

**M** = Month Code

(A=Jan, B=Feb, C=Mar, D=Apl, E=May, F=Jun, G=Jul, H=Aug,

I=Sep, J=Oct, K=Nov, L=Dec)

5/6

L = Lot Code

Version: A07



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